

4.5 A, 600 V very fast IGBT with Ultrafast diode

Datasheet - production data

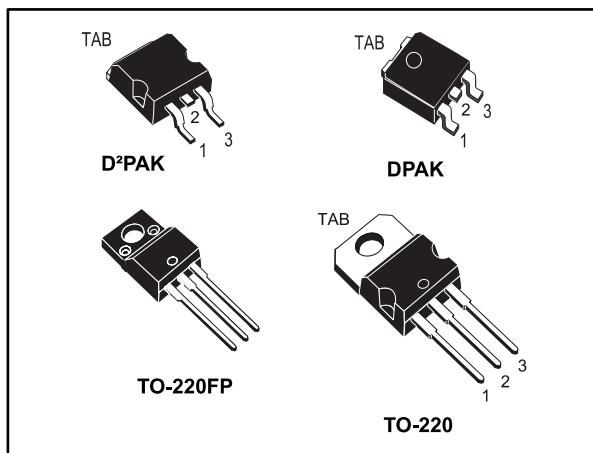


Figure 1: Internal schematic diagram

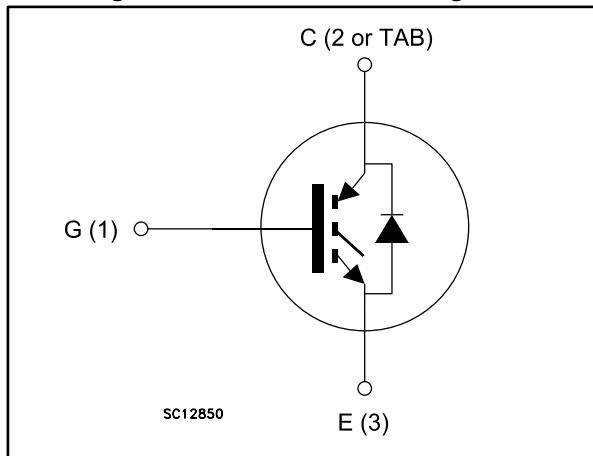


Table 1: Device summary

Order code	Marking	Package	Packing
STGB3HF60HD	GB3HF60HD	D ² PAK	Tape and reel
STGD3HF60HDT4	GD3HF60HD	DPAK	Tape and reel
STGF3HF60HD	GF3HF60HD	TO-220FP	Tube
STGP3HF60HD	GP3HF60HD	TO-220	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value			Unit
		DPAK	D²PAK TO-220	TO-220FP	
V _{CES}	Collector-emitter voltage ($V_{GE} = 0$)	600			V
I _c ⁽¹⁾	Continuous collector current at $T_c = 25^\circ\text{C}$		7.5		A
I _c ⁽¹⁾	Continuous collector current at $T_c = 100^\circ\text{C}$		4.5		A
I _{CL} ⁽²⁾	Turn-off latching current		18		A
I _{CP} ⁽³⁾	Pulsed collector current		18		A
V _{GE}	Gate-emitter voltage		± 20		V
I _F	Diode RMS forward current at $T_c = 25^\circ\text{C}$		10		A
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms}$ sinusoidal		25		A
P _{TOT}	Total dissipation at $T_c = 25^\circ\text{C}$	38		18	W
T _{STG}	Storage temperature range			- 55 to 150	
T _j	Operating junction temperature range				°C

Notes:

⁽¹⁾Calculated according to the iterative formula:

$$I_C(T_c) = \frac{T_{j(max)} - T_c}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_c))}$$

⁽²⁾V_{clamp} = 80 %, (V_{CES}), T_j = 150 °C, R_G = 10 Ω, V_{GE} = 15 V.

⁽³⁾Pulse width limited by maximum junction temperature range.

Table 3: Thermal data

Symbol	Parameter	Value			Unit
		DPAK	D²PAK TO-220	TO-220FP	
R _{thj-case}	Thermal resistance junction-case IGBT	3.3		6.9	°C/W
	Thermal resistance junction-case diode	5		8	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	100		62.5	°C/W

2 Electrical characteristics

($T_j=25^\circ\text{C}$ unless otherwise specified).

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{CES}}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1 \text{ mA}$	600			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE} = 15 \text{ V}, I_C = 0.5 \text{ A}, T_j = 125^\circ\text{C}$		1.4		V
		$V_{GE} = 15 \text{ V}, I_C = 1.5 \text{ A}$		2.45	2.95	
		$V_{GE} = 15 \text{ V}, I_C = 1.5 \text{ A}, T_j = 125^\circ\text{C}$		1.85		
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 250 \mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600 \text{ V}$			250	μA
		$V_{CE} = 600 \text{ V}, T_j = 125^\circ\text{C}$			1	mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20 \text{ V}$			± 100	nA
g_{fs}	Forward transconductance	$V_{CE} = 15 \text{ V}, I_C = 1.5 \text{ A}$		1.5		S

Table 5: Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GE} = 0$	-	152	-	pF
C_{oes}	Output capacitance		-	14	-	pF
C_{res}	Reverse transfer capacitance		-	3	-	pF
Q_g	Total gate charge	$V_{CE} = 480 \text{ V}, I_C = 1.5 \text{ A}, V_{GE} = 15 \text{ V}$ (see Figure 18: "Gate charge test circuit")	-	12	-	nC
Q_{ge}	Gate-emitter charge		-	2	-	nC
Q_{gc}	Gate-collector charge		-	6	-	nC

Table 6: Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 400 \text{ V}, I_C = 1.5 \text{ A}$ $R_G = 100 \Omega, V_{GE} = 15 \text{ V}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	11	-	ns
t_r	Current rise time		-	4	-	ns
$(di/dt)on$	Turn-on current slope		-	285	-	A/ μs
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 400 \text{ V}, I_C = 1.5 \text{ A}$ $R_G = 100 \Omega, V_{GE} = 15 \text{ V}$ $T_j = 125^\circ\text{C}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	10	-	ns
t_r	Current rise time		-	5	-	ns
$(di/dt)on$	Turn-on current slope		-	265	-	A/ μs
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 400 \text{ V}, I_C = 1.5 \text{ A}$, $R_{GE} = 100 \Omega, V_{GE} = 15 \text{ V}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	26	-	ns
$t_{d(off)}$	Turn-off delay time		-	60	-	ns
t_f	Current fall time		-	50	-	ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 400 \text{ V}, I_C = 1.5 \text{ A}$, $R_{GE} = 100 \Omega, V_{GE} = 15 \text{ V}$, $T_j = 125^\circ\text{C}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	64	-	ns
$t_{d(off)}$	Turn-off delay time		-	69	-	ns
t_f	Current fall time		-	71	-	ns

Table 7: Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CC} = 400 \text{ V}, I_C = 1.5 \text{ A}$ $R_G = 100 \Omega, V_{GE} = 15 \text{ V}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	19	-	μJ
$E_{off}^{(2)}$ E_{ts}	Turn-off switching energy		-	12	-	μJ
E_{ts}	Total switching energy		-	31	-	μJ
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CC} = 400 \text{ V}, I_C = 1.5 \text{ A}$ $R_G = 100 \Omega, V_{GE} = 15 \text{ V}$, $T_j = 125^\circ\text{C}$ (see Figure 17: "Test circuit for inductive load switching" Figure 19: "Switching waveform")	-	38	-	μJ
$E_{off}^{(2)}$	Turn-off switching energy		-	35	-	μJ
E_{ts}	Total switching energy		-	73	-	μJ

Notes:

⁽¹⁾Eon is the turn-on energy when a typical diode is used in the test circuit in [Figure 17: "Test circuit for inductive load switching"](#). If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs and diode are at the same temperature (25 °C and 125 °C).

⁽²⁾Turn-off energy include also the tail of the collector current.

Electrical characteristics

STGB3HF60HD, STGD3HF60HDT4,
STGF3HF60HD, STGP3HF60HD

Table 8: Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	$I_F = 1.5 \text{ A}$	-	1.4	1.8	V
		$I_F = 1.5 \text{ A}, T_j = 125 \text{ }^\circ\text{C}$	-	1.15		
t_{rr}	Reverse recovery time		-	85		ns
Q_{rr}	Reverse recovery charge	$I_F = 1.5 \text{ A}, V_R = 40 \text{ V},$ $di/dt = 100 \text{ A}/\mu\text{s}$ (see Figure 20: "Diode reverse recovery waveform")	-	124		nC
			-	3		A
t_{rr}	Reverse recovery time		-	114		ns
Q_{rr}	Reverse recovery charge	$I_F = 1.5 \text{ A}, V_R = 40 \text{ V},$ $T_j = 125 \text{ }^\circ\text{C}, di/dt = 100 \text{ A}/\mu\text{s}$ (see Figure 20: "Diode reverse recovery waveform")	-	194		nC
			-	3.5		A
I_{rrm}	Reverse recovery current					

2.1 Electrical characteristics (curves)

Figure 2: Output characteristics

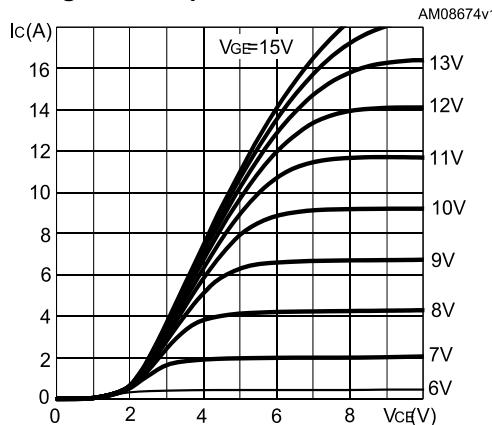


Figure 3: Output characteristic details

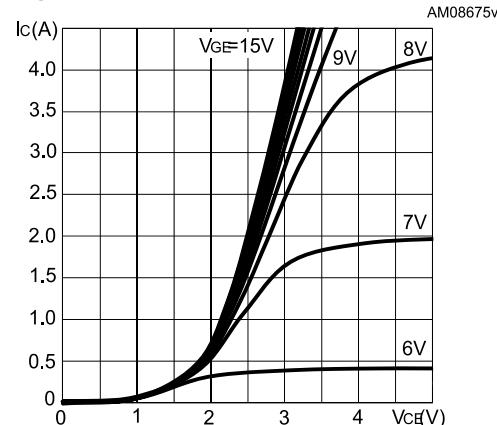


Figure 4: Transfer characteristics

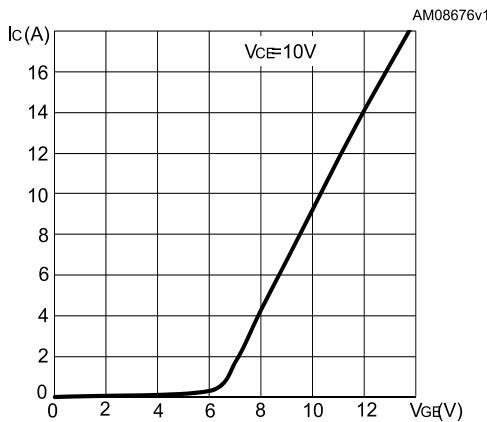


Figure 5: Collector-emitter on voltage vs collector current

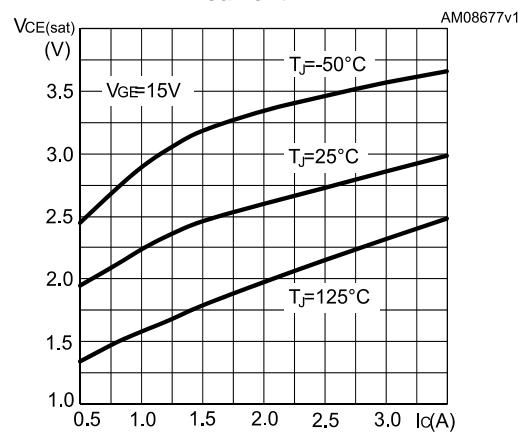


Figure 6: Collector-emitter on voltage vs temperature

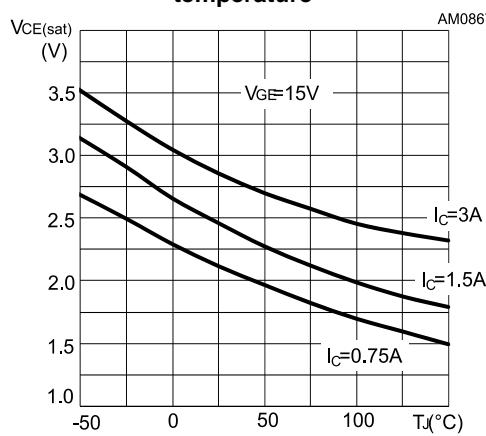
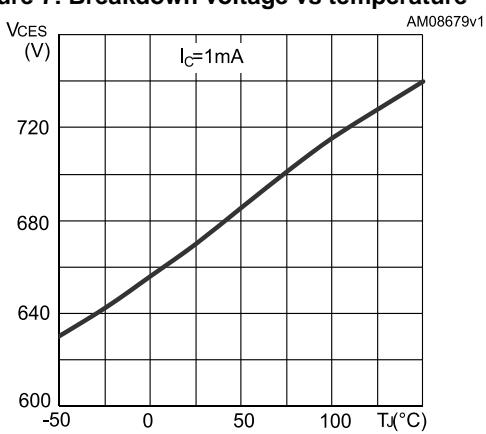


Figure 7: Breakdown voltage vs temperature



Electrical characteristics

**STGB3HF60HD, STGD3HF60HDT4,
STGF3HF60HD, STGP3HF60HD**

Figure 8: Gate threshold voltage vs temperature

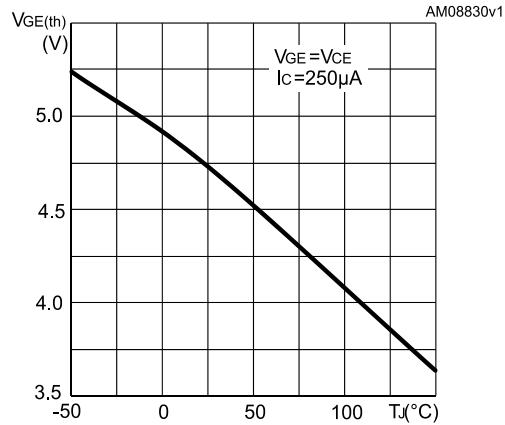


Figure 9: Gate charge vs gate-emitter voltage

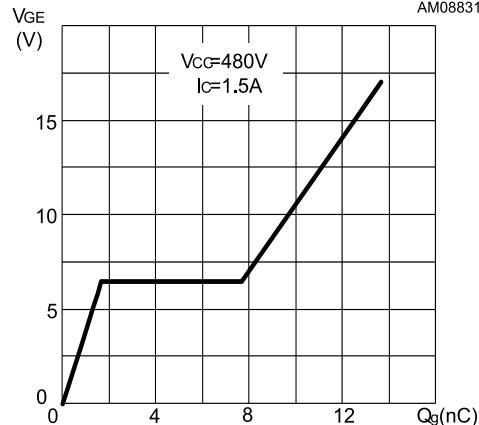


Figure 10: Capacitance variations

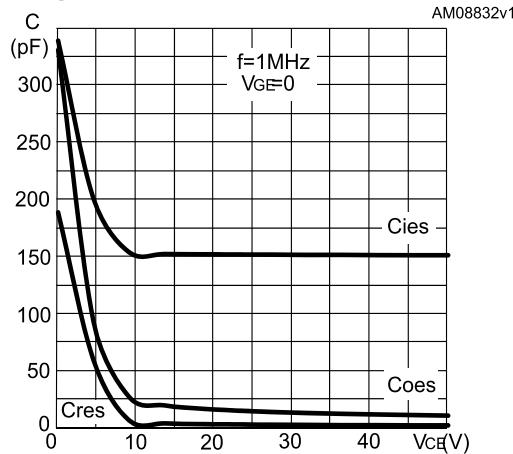


Figure 11: Switching energy vs collector current

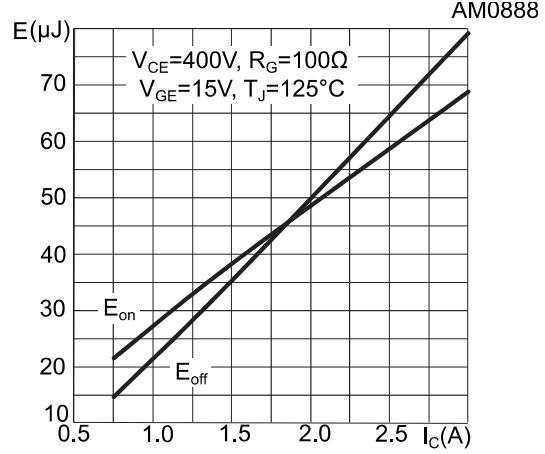


Figure 12: Switching energy vs gate resistance

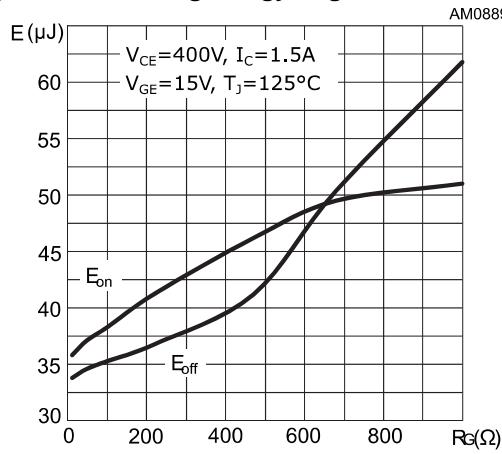


Figure 13: Switching energy vs temperature

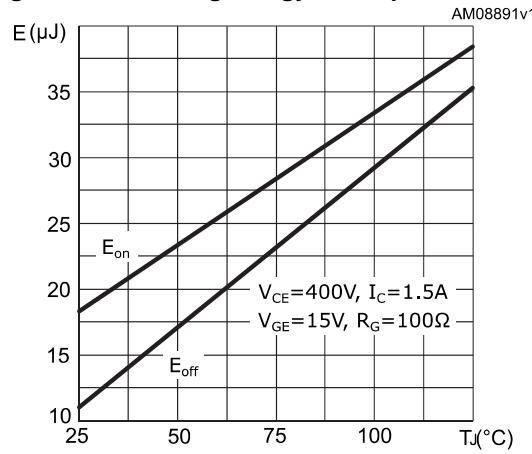
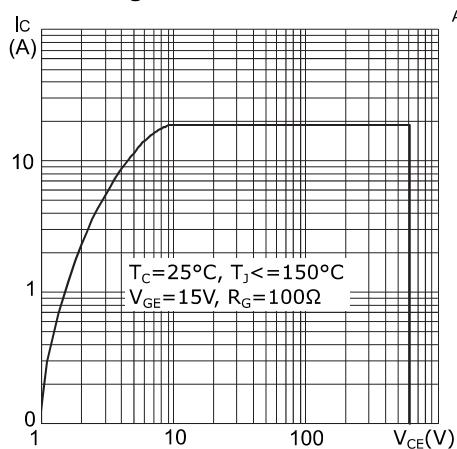
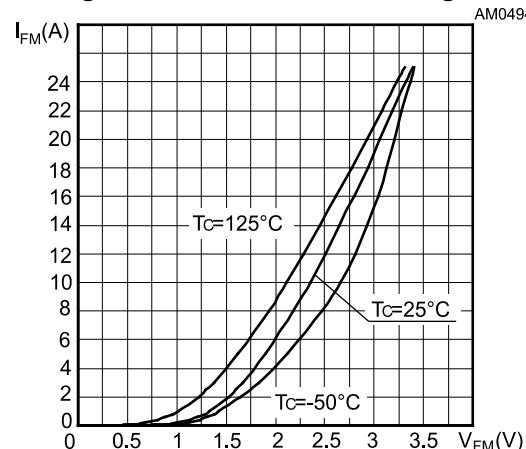


Figure 14: Turn-off SOA



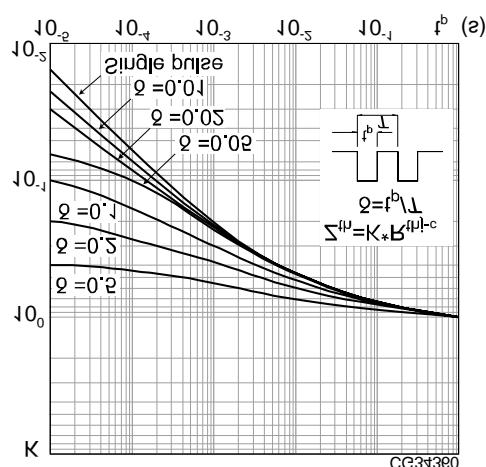
AM08836v1

Figure 15: Diode forward on voltage



AM04940v1

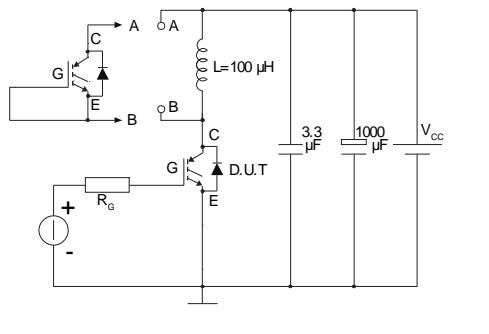
Figure 16: Thermal impedance



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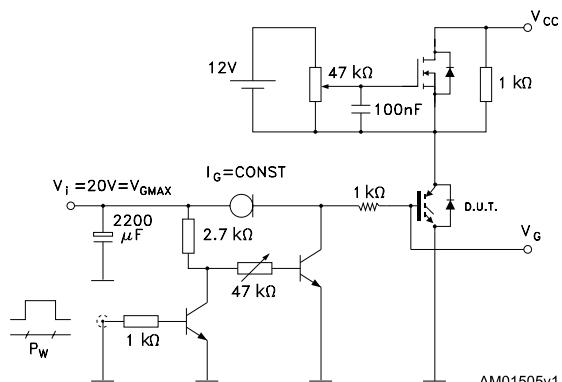
3 Test circuits

Figure 17: Test circuit for inductive load switching



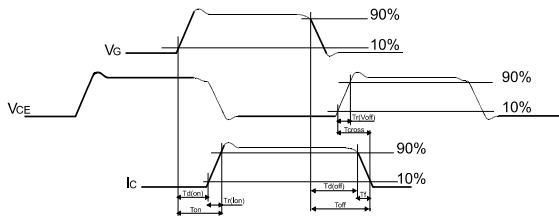
AM01504v1

Figure 18: Gate charge test circuit



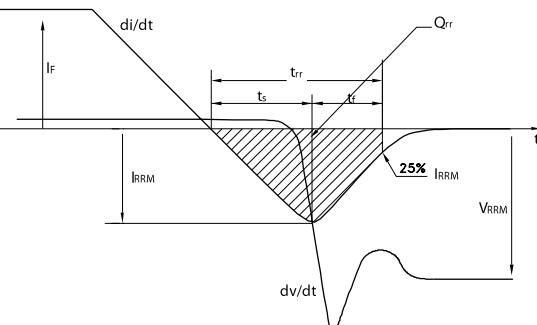
AM01505v1

Figure 19: Switching waveform



AM01506v1

Figure 20: Diode reverse recovery waveform



AM01507v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

4.1 D²PAK (TO-263) package information

Figure 21: D²PAK (TO-263) type A package outline

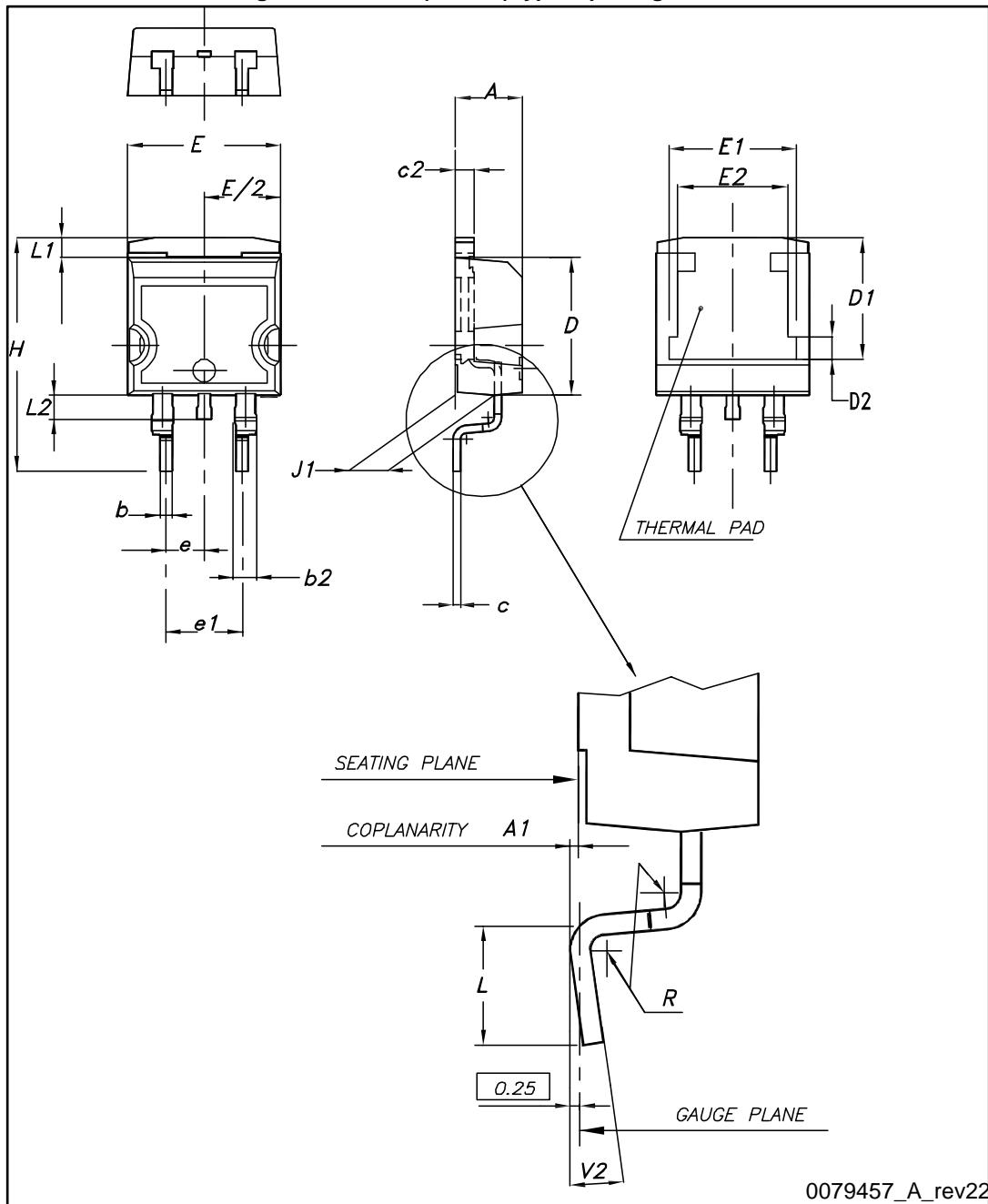
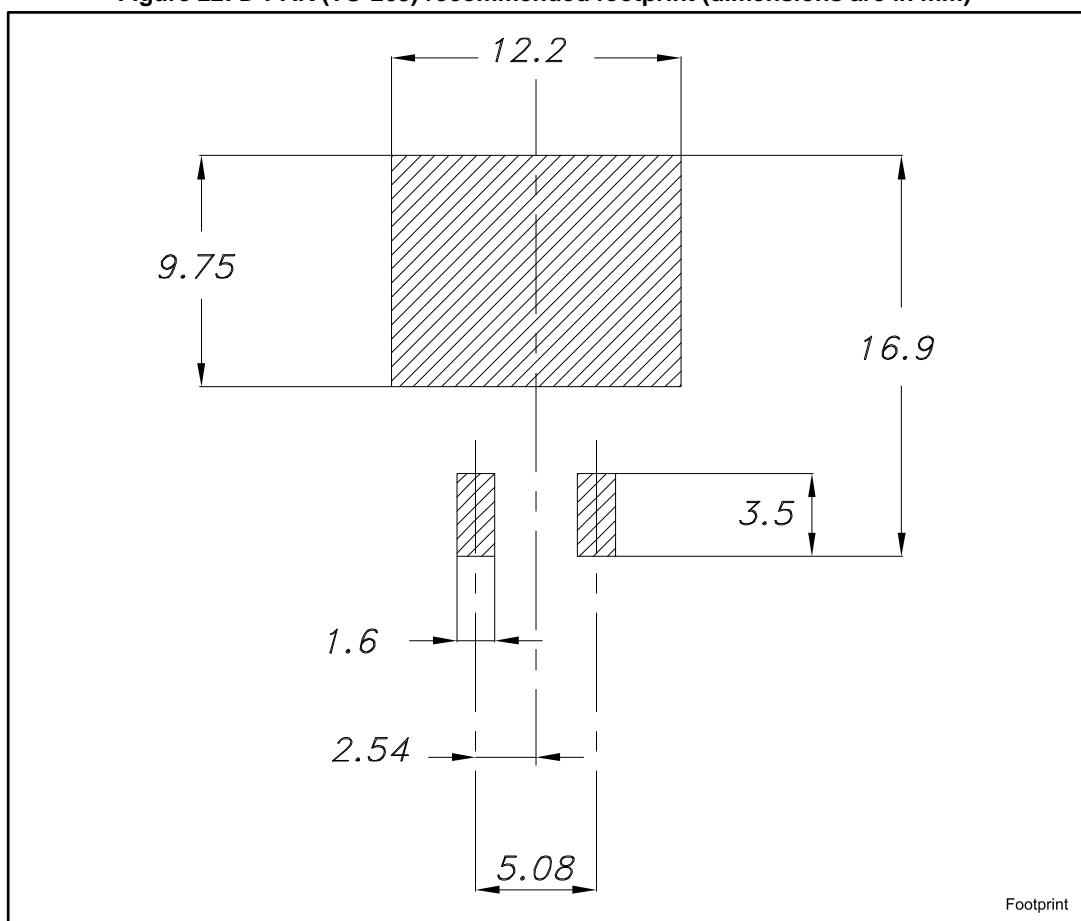


Table 9: D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10		10.40
E1	8.50	8.70	8.90
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 22: D²PAK (TO-263) recommended footprint (dimensions are in mm)



4.2 D²PAK (TO-263) packing information

Figure 23: Tape outline

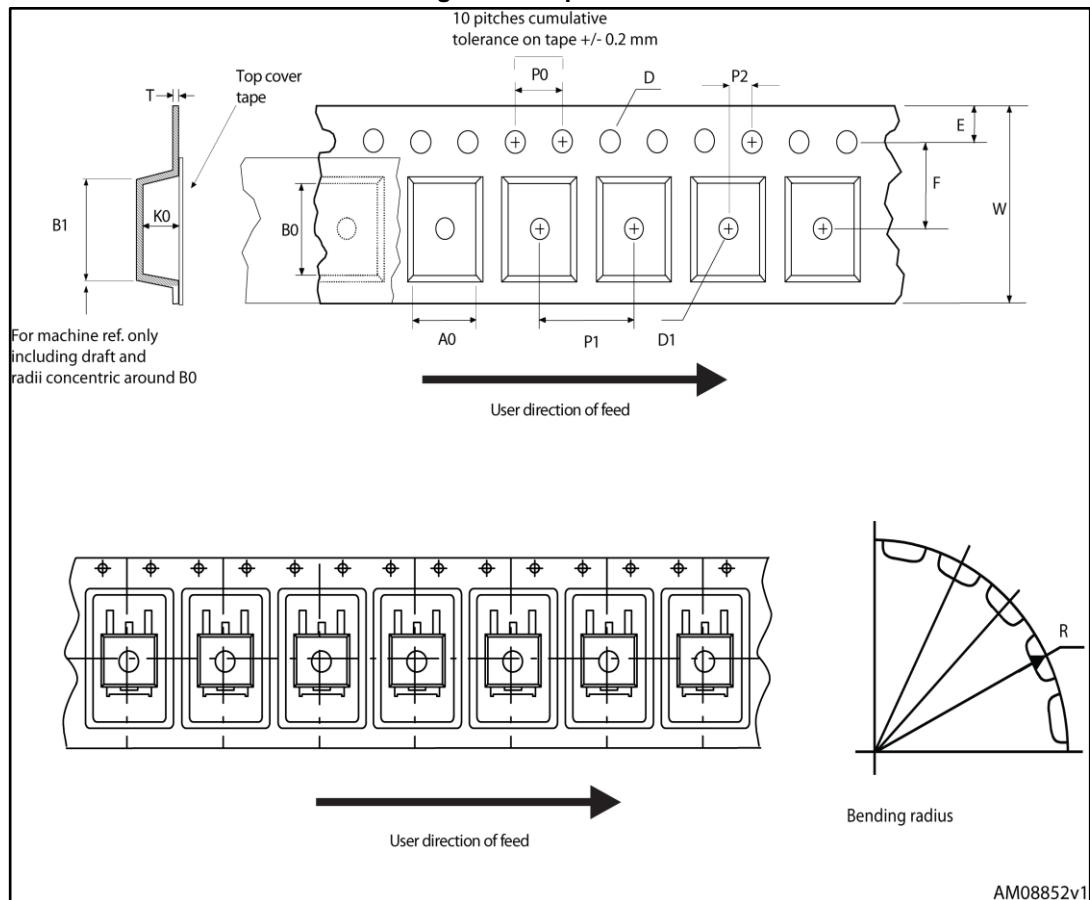


Figure 24: Reel outline

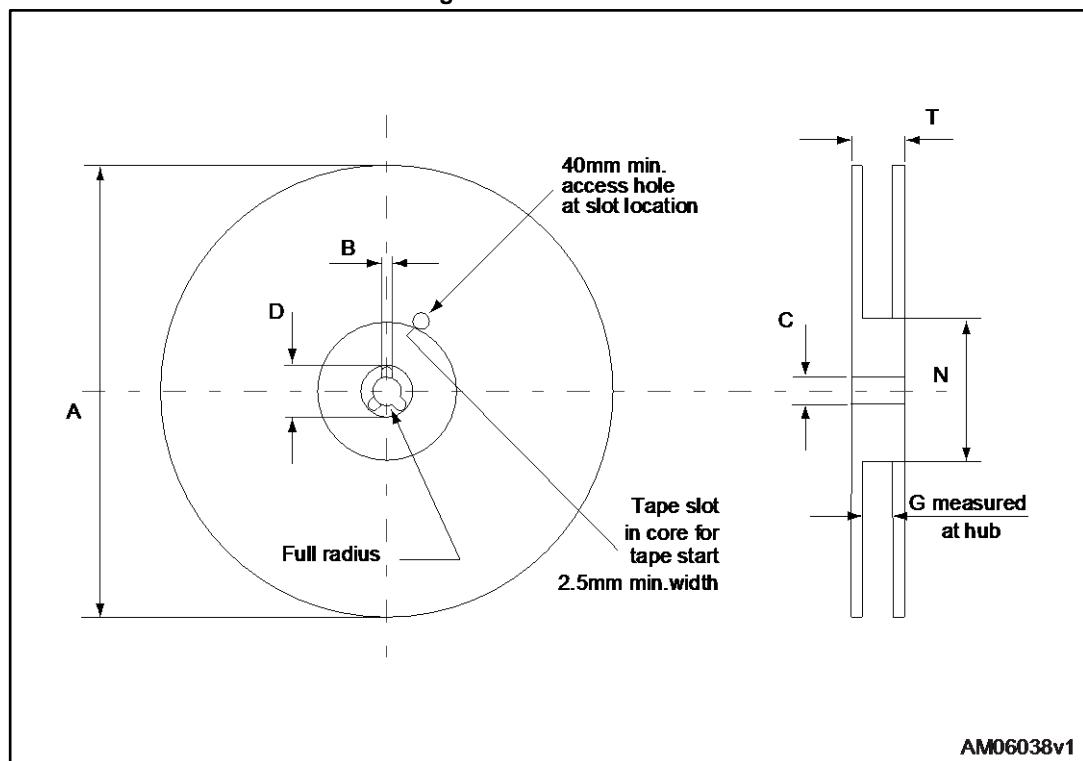
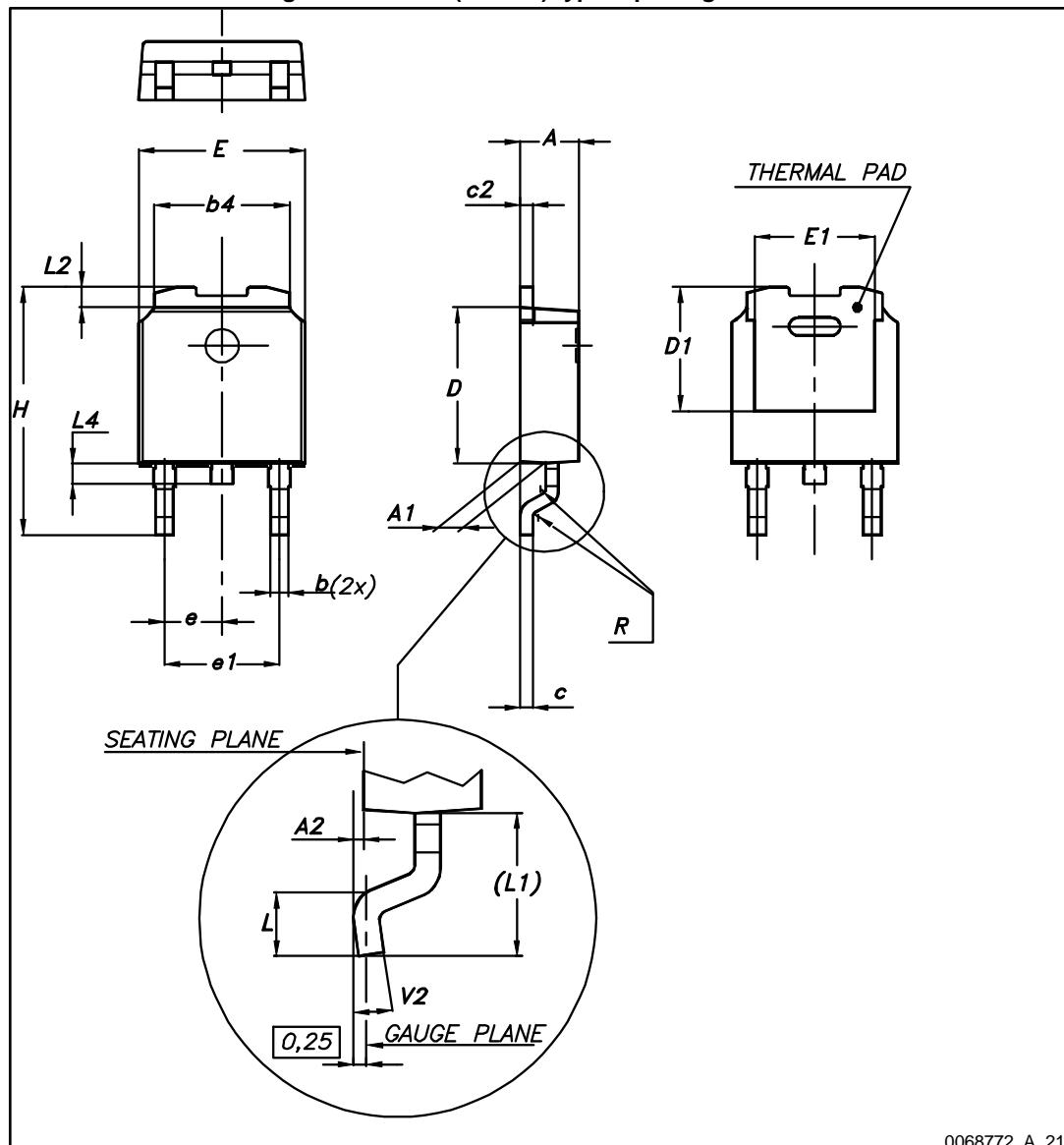


Table 10: D²PAK tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

4.3 DPAK (TO-252) type A package information

Figure 25: DPAK (TO-252) type A package outline

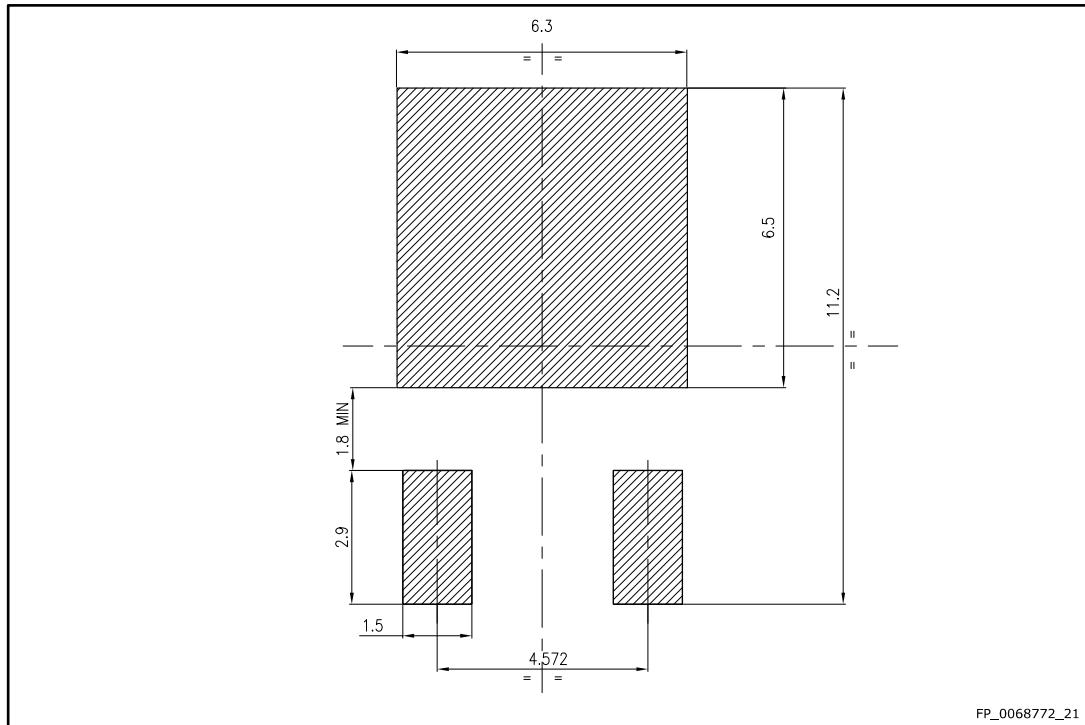


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Table 11: DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 26: DPAK (TO-252) recommended footprint (dimensions are in mm)



4.4 DPAK (TO-252) packing information

Figure 27: DPAK (TO-252) tape outline

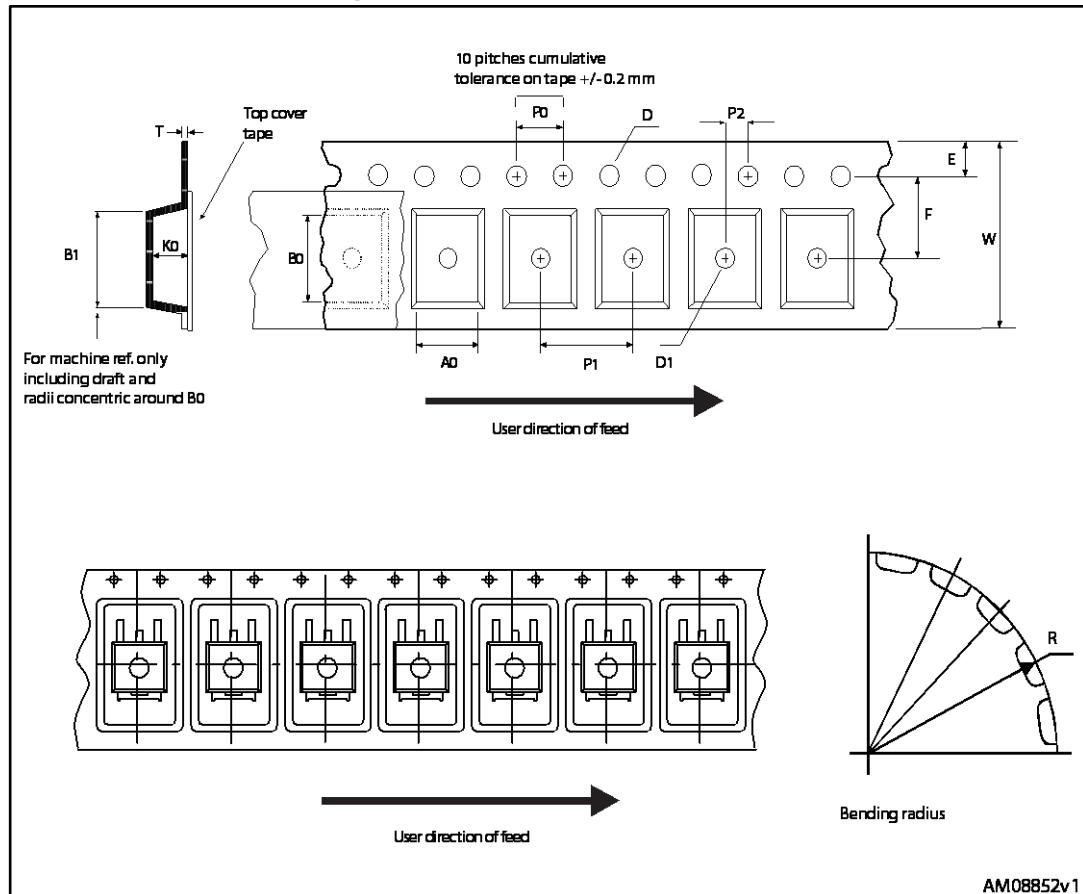


Figure 28: DPAK (TO-252) reel outline

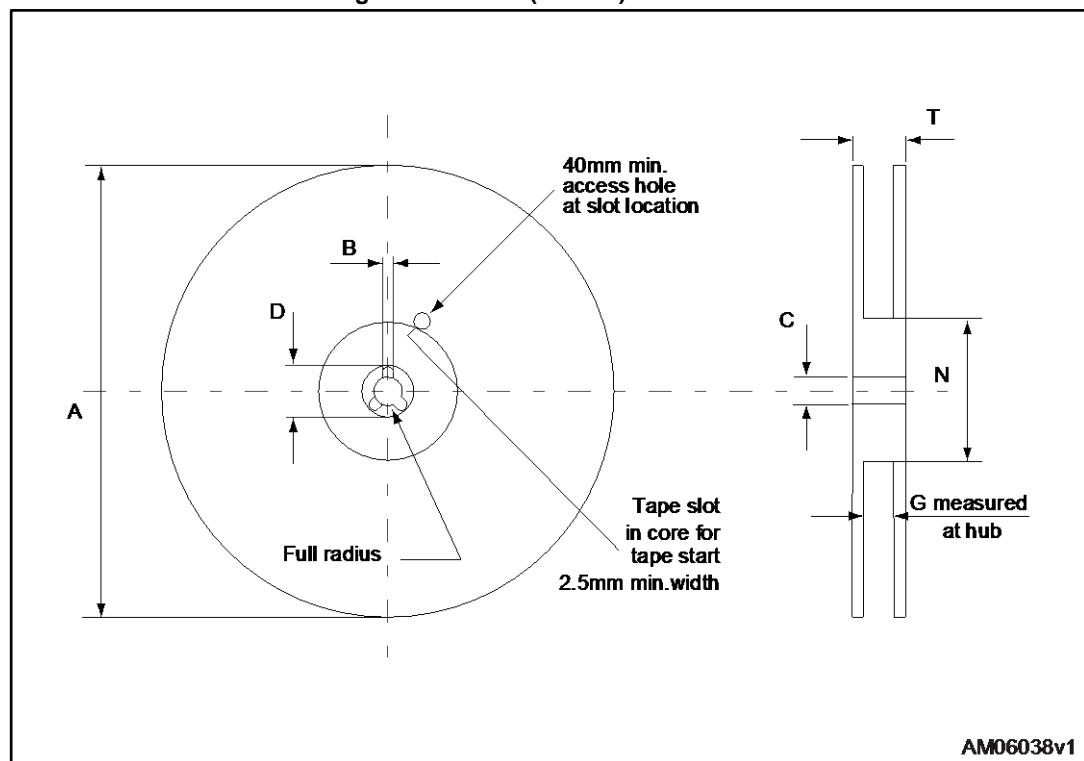


Table 12: DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.5 TO-220FP package information

Figure 29: TO-220FP package outline

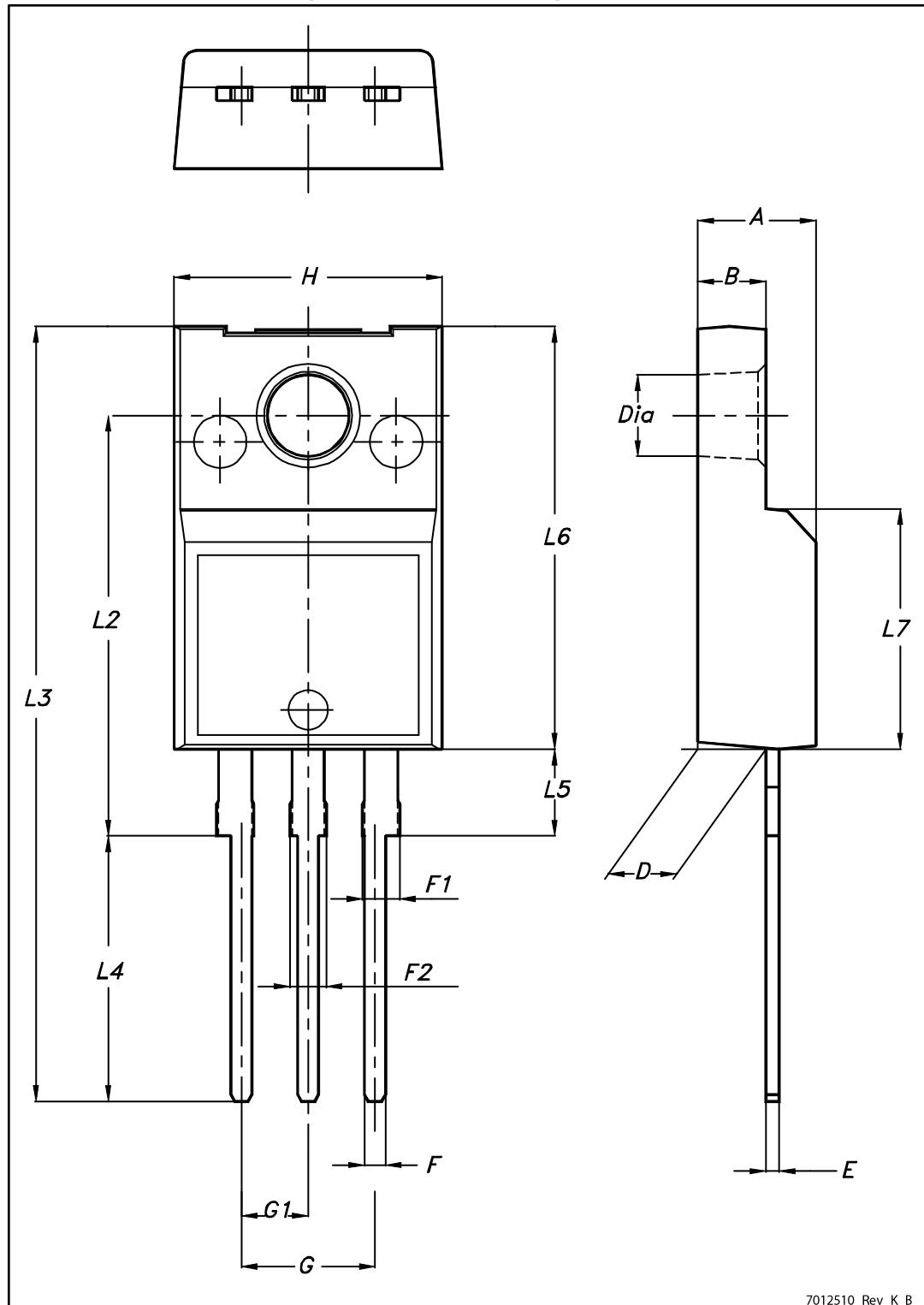
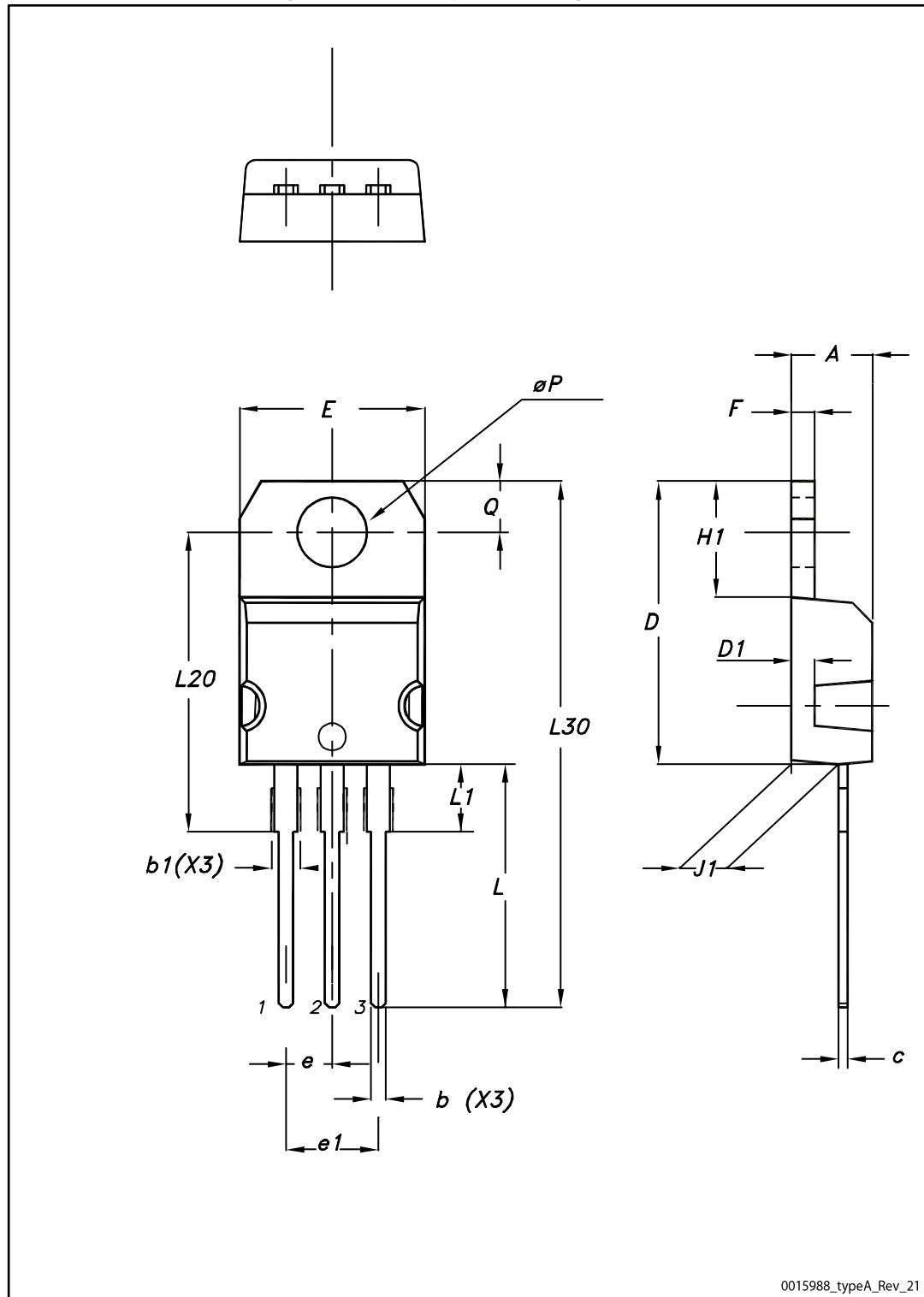


Table 13: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

4.6 TO-220 type A package information

Figure 30: TO-220 type A package outline



0015988_typeA_Rev_21

Table 14: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

5 Revision history

Table 15: Document revision history

Date	Revision	Changes
29-Jun-2010	1	First release.
09-Sep-2010	2	Some values changed in <i>Table 2</i> .
22-Dec-2010	3	Document status promoted from preliminary data to datasheet.
24-Sep-2013	4	Added device in TO-220. Updated <i>Table 1: Device summary</i> , <i>Table 3: Thermal data</i> and <i>Section 4: Package mechanical data</i> accordingly.
19-Sep-2016	5	Added the order codes STGB3HF60HD and STGF3HF60HD. Added TO-220FP and D ² PAK packages. Updated <i>Table 1: "Device summary"</i> , <i>Section 1: "Electrical ratings"</i> , <i>Section 4: "Package information"</i> . Minor text changes.